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Details

Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, I ² C, LINbus, SCI, SPI, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	121
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	80K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 53x10/12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/spc560b60l5c6e0x

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Table 3. SPC560B54/6x series block summary (continued)

Block	Function
Mode entry module (MC_ME)	Provides a mechanism for controlling the device operational mode and mode transition sequences in all functional states; also manages the power control unit, reset generation module and clock generation module, and holds the configuration, control and status registers accessible for applications
Non-maskable interrupt (NMI)	Handles external events that must produce an immediate response, such as power down detection
Periodic interrupt timer (PIT)	Produces periodic interrupts and triggers
Power control unit (MC_PCU)	Reduces the overall power consumption by disconnecting parts of the device from the power supply via a power switching device; device components are grouped into sections called "power domains" which are controlled by the PCU
Real-time counter (RTC)	A free running counter used for time keeping applications, the RTC can be configured to generate an interrupt at a predefined interval independent of the mode of operation (run mode or low-power mode)
Reset generation module (MC_RGM)	Centralizes reset sources and manages the device reset sequence of the device
Static random-access memory (SRAM)	Provides storage for program code, constants, and variables
System integration unit lite (SIUL)	Provides control over all the electrical pad controls and up to 32 ports with 16 bits of bidirectional, general-purpose input and output signals and supports up to 32 external interrupts with trigger event configuration
System status and configuration module (SSCM)	Provides system configuration and status data (such as memory size and status, device mode and security status), device identification data, debug status port enable and selection, and bus and peripheral abort enable/disable
System timer module (STM)	Provides a set of output compare events to support AUTOSAR (Automotive Open System Architecture) and operating system tasks
Software watchdog timer (SWT)	Provides protection from runaway code
Wakeup unit (WKPU)	The wakeup unit supports up to 27 external sources that can generate interrupts or wakeup events, of which 1 can cause non-maskable interrupt requests or wakeup events.



Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function ⁽¹⁾	Function	Peripheral	I/O direction ⁽²⁾	Pad type	RESET configuration ⁽³⁾	Pin number			
								LQFP 100	LQFP 144	LQFP 176	LBGA 208 ⁽⁴⁾
PA[8]	PCR[8]	AF0 AF1 AF2 AF3 — N/A ⁽⁷⁾ —	GPIO[8] E0UC[8] E0UC[14] — EIRQ[3] ABS[0] LIN3RX	SIUL eMIOS_0 eMIOS_0 — SIUL BAM LINFlex_3	I/O I/O I/O — I I I	S	Input, weak pull-up	72	105	129	C16
PA[9]	PCR[9]	AF0 AF1 AF2 AF3 N/A ⁽⁷⁾	GPIO[9] E0UC[9] — CS2_1 FAB	SIUL eMIOS_0 — DSPI_1 BAM	I/O I/O — O I	S	Pull-down	73	106	130	C15
PA[10]	PCR[10]	AF0 AF1 AF2 AF3 —	GPIO[10] E0UC[10] SDA LIN2TX ADC1_S[2]	SIUL eMIOS_0 I ² C_0 LINFlex_2 ADC_1	I/O I/O I/O O I	J	Tristate	74	107	131	B16
PA[11]	PCR[11]	AF0 AF1 AF2 AF3 — — —	GPIO[11] E0UC[11] SCL — EIRQ[16] LIN2RX ADC1_S[3]	SIUL eMIOS_0 I ² C_0 — SIUL LINFlex_2 ADC_1	I/O I/O I/O — I I I	J	Tristate	75	108	132	B15



Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function ⁽¹⁾	Function	Peripheral	I/O direction ⁽²⁾	Pad type	RESET configuration ⁽³⁾	Pin number			
								LQFP 100	LQFP 144	LQFP 176	LBGA 208 ⁽⁴⁾
PD[8]	PCR[56]	AF0	GPIO[56]	SIUL	I	I	Tristate	49	71	87	T15
		AF1	—	—	—						
		AF2	—	—	—						
		AF3	—	—	—						
		—	ADC0_P[12]	ADC_0	I						
		—	ADC1_P[12]	ADC_1	I						
PD[9]	PCR[57]	AF0	GPIO[57]	SIUL	I	I	Tristate	56	78	94	N15
		AF1	—	—	—						
		AF2	—	—	—						
		AF3	—	—	—						
		—	ADC0_P[13]	ADC_0	I						
		—	ADC1_P[13]	ADC_1	I						
PD[10]	PCR[58]	AF0	GPIO[58]	SIUL	I	I	Tristate	57	79	95	N14
		AF1	—	—	—						
		AF2	—	—	—						
		AF3	—	—	—						
		—	ADC0_P[14]	ADC_0	I						
		—	ADC1_P[14]	ADC_1	I						
PD[11]	PCR[59]	AF0	GPIO[59]	SIUL	I	I	Tristate	58	80	96	N16
		AF1	—	—	—						
		AF2	—	—	—						
		AF3	—	—	—						
		—	ADC0_P[15]	ADC_0	I						
		—	ADC1_P[15]	ADC_1	I						

Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function ⁽¹⁾	Function	Peripheral	I/O direction ⁽²⁾	Pad type	RESET configuration ⁽³⁾	Pin number			
								LQFP 100	LQFP 144	LQFP 176	LBGA 208 ⁽⁴⁾
PH[4]	PCR[116]	AF0 AF1 AF2 AF3	GPIO[116] E1UC[6] — —	SIUL eMIOS_1 — —	I/O I/O — —	M	Tristate	—	134	162	A6
PH[5]	PCR[117]	AF0 AF1 AF2 AF3	GPIO[117] E1UC[7] — —	SIUL eMIOS_1 — —	I/O I/O — —	S	Tristate	—	135	163	B6
PH[6]	PCR[118]	AF0 AF1 AF2 AF3	GPIO[118] E1UC[8] — MA[2]	SIUL eMIOS_1 — ADC_0	I/O I/O — O	M	Tristate	—	136	164	D5
PH[7]	PCR[119]	AF0 AF1 AF2 AF3	GPIO[119] E1UC[9] CS3_2 MA[1]	SIUL eMIOS_1 DSPI_2 ADC_0	I/O I/O O O	M	Tristate	—	137	165	C5
PH[8]	PCR[120]	AF0 AF1 AF2 AF3	GPIO[120] E1UC[10] CS2_2 MA[0]	SIUL eMIOS_1 DSPI_2 ADC_0	I/O I/O O O	M	Tristate	—	138	166	A5
PH[9] ⁽¹⁰⁾	PCR[121]	AF0 AF1 AF2 AF3	GPIO[121] — TCK —	SIUL — JTAGC —	I/O — I —	S	Input, weak pull-up	88	127	155	B8

3.8 Nexus 2+ pins

In the LBGA208 package, eight additional debug pins are available (see [Table 7](#)).

Table 7. Nexus 2+ pin descriptions

Port pin	Function	I/O direction	Pad type	Function after reset	Pin number		
					LQFP 100	LQFP 144	LBGA 208 ⁽¹⁾
MCKO	Message clock out	O	F	—	—	—	T4
MDO0	Message data out 0	O	M	—	—	—	H15
MDO1	Message data out 1	O	M	—	—	—	H16
MDO2	Message data out 2	O	M	—	—	—	H14
MDO3	Message data out 3	O	M	—	—	—	H13
EVTI	Event in	I	M	Pull-up	—	—	K1
EVTO	Event out	O	M	—	—	—	L4
MSEO	Message start/end out	O	M	—	—	—	G16

1. LBGA208 available only as development package for Nexus2+.

Table 14. Recommended operating conditions (5.0 V)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max	
V_{SS}	S R	Digital ground on VSS_HV pins	—	0	0	V
$V_{DD}^{(1)}$	S R	Voltage on VDD_HV pins with respect to ground (V_{SS})	—	4.5	5.5	V
			Voltage drop ⁽²⁾	3.0	5.5	
$V_{SS_LV}^{(3)}$	S R	Voltage on VSS_LV (low voltage digital supply) pins with respect to ground (V_{SS})	—	$V_{SS} - 0.1$	$V_{SS} + 0.1$	V
$V_{DD_BV}^{(4)}$	S R	Voltage on VDD_BV pin (regulator supply) with respect to ground (V_{SS})	—	4.5	5.5	V
			Voltage drop ⁽²⁾	3.0	5.5	
			Relative to V_{DD}	3.0	$V_{DD} + 0.1$	
V_{SS_ADC}	S R	Voltage on VSS_HV_ADC0, VSS_HV_ADC1 (ADC reference) pin with respect to ground (V_{SS})	—	$V_{SS} - 0.1$	$V_{SS} + 0.1$	V
$V_{DD_ADC}^{(5)}$	S R	Voltage on VDD_HV_ADC0, VDD_HV_ADC1 (ADC reference) with respect to ground (V_{SS})	—	4.5	5.5	V
			Voltage drop ⁽²⁾	3.0	5.5	
			Relative to V_{DD}	$V_{DD} - 0.1$	$V_{DD} + 0.1$	
V_{IN}	S R	Voltage on any GPIO pin with respect to ground (V_{SS})	—	$V_{SS} - 0.1$	—	V
			Relative to V_{DD}	—	$V_{DD} + 0.1$	
I_{INJPAD}	S R	Injected input current on any pin during overload condition	—	-5	5	mA
I_{INJSUM}	S R	Absolute sum of all injected input currents during overload condition	—	-50	50	
TV_{DD}	S R	V_{DD} slope to ensure correct power up ⁽⁶⁾	—	3.0 ⁽⁷⁾	250×10^3 (0.25 [V/μs])	V/s

- 100 nF capacitance needs to be provided between each V_{DD}/V_{SS} pair.
- Full device operation is guaranteed by design when the voltage drops below 4.5 V down to 3.0 V. However, certain analog electrical characteristics will not be guaranteed to stay within the stated limits.
- 330 nF capacitance needs to be provided between each V_{DD_LV}/V_{SS_LV} supply pair.
- 470 nF capacitance needs to be provided between V_{DD_BV} and the nearest V_{SS_LV} (higher value may be needed depending on external regulator characteristics). While the supply voltage ramps up, the slope on V_{DD_BV} should be less than $0.9V_{DD_HV}$ in order to ensure the device does not enter regulator bypass mode.
- 100 nF capacitance needs to be provided between V_{DD_ADC}/V_{SS_ADC} pair.
- Guaranteed by device validation.
- Minimum value of TV_{DD} must be guaranteed until V_{DD} reaches 2.6 V (maximum value of V_{PORH}).

Note: RAM data retention is guaranteed with V_{DD_LV} not below 1.08 V.

4.5 Thermal characteristics

4.5.1 External ballast resistor recommendations

External ballast resistor on V_{DD_BV} pin helps in reducing the overall power dissipation inside the device. This resistor is required only when maximum power consumption exceeds the limit imposed by package thermal characteristics.

As stated in [Table 15](#) LQFP thermal characteristics, considering a thermal resistance of LQFP144 as $48.3\text{ }^{\circ}\text{C/W}$, at ambient temperature $T_A = 125\text{ }^{\circ}\text{C}$, the junction temperature T_j will cross $150\text{ }^{\circ}\text{C}$ if the total power dissipation is greater than $(150 - 125)/48.3 = 517\text{ mW}$. Therefore, the total device current I_{DDMAX} at $125\text{ }^{\circ}\text{C}/5.5\text{ V}$ must not exceed 94.1 mA (i.e., P_D/V_{DD}). Assuming an average $I_{DD}(V_{DD_HV})$ of $15\text{--}20\text{ mA}$ consumption typically during device RUN mode, the LV domain consumption $I_{DD}(V_{DD_BV})$ is thus limited to $I_{DDMAX} - I_{DD}(V_{DD_HV})$, i.e., 80 mA .

Therefore, respecting the maximum power allowed as explained in [Section 4.5.2: Package thermal characteristics](#), it is recommended to use this resistor only in the $125\text{ }^{\circ}\text{C}/5.5\text{ V}$ operating corner as per the following guidelines:

- If $I_{DD}(V_{DD_BV}) < 80\text{ mA}$, then no resistor is required.
- If $80\text{ mA} < I_{DD}(V_{DD_BV}) < 90\text{ mA}$, then $4\text{ }\Omega$ resistor can be used.
- If $I_{DD}(V_{DD_BV}) > 90\text{ mA}$, then $8\text{ }\Omega$ resistor can be used.

Using resistance in the range of $4\text{--}8\text{ }\Omega$, the gain will be around $10\text{--}20\%$ of total consumption on V_{DD_BV} . For example, if $8\text{ }\Omega$ resistor is used, then power consumption when $I_{DD}(V_{DD_BV})$ is 110 mA is equivalent to power consumption when $I_{DD}(V_{DD_BV})$ is 90 mA (approximately) when resistor not used.

In order to ensure correct power up, the minimum V_{DD_BV} to be guaranteed is 30 ms/V . If the supply ramp is slower than this value, then LVDHV3B monitoring ballast supply V_{DD_BV} pin gets triggered leading to device reset. Until the supply reaches certain threshold, this low voltage detector (LVD) generates destructive reset event in the system. This threshold depends on the maximum $I_{DD}(V_{DD_BV})$ possible across the external resistor.

4.5.2 Package thermal characteristics

Table 15. LQFP thermal characteristics⁽¹⁾

Symbol		C	Parameter	Conditions ⁽²⁾	Pin count	Value			Unit
						Min	Typ	Max	
R _{θJA}	CC	D	Thermal resistance, junction-to-ambient natural convection ⁽³⁾	Single-layer board — 1s	100	—	—	64	°C/W
					144	—	—	64	
					176	—	—	64	
				Four-layer board — 2s2p	100	—	—	49.7	
					144	—	—	48.3	
					176	—	—	47.3	

Table 24. I/O weight⁽¹⁾ (continued)

Supply segment			Pad	LQFP176				LQFP144/100			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
LQFP 176	LQFP 144	LQFP 100		SRC ⁽²⁾ = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
3	2	2	PB[9]	1%	—	1%	—	1%	—	1%	—
			PB[8]	1%	—	1%	—	1%	—	1%	—
			PB[10]	5%	—	6%	—	6%	—	7%	—
		—	PF[0]	5%	—	6%	—	6%	—	8%	—
			PF[1]	5%	—	6%	—	7%	—	8%	—
			PF[2]	6%	—	7%	—	7%	—	9%	—
			PF[3]	6%	—	7%	—	8%	—	9%	—
			PF[4]	6%	—	7%	—	8%	—	10%	—
			PF[5]	6%	—	7%	—	9%	—	10%	—
			PF[6]	6%	—	7%	—	9%	—	11%	—
			PF[7]	6%	—	7%	—	9%	—	11%	—
	—	—	PJ[3]	6%	—	7%	—	—	—	—	—
	—	—	PJ[2]	6%	—	7%	—	—	—	—	—
	—	—	PJ[1]	6%	—	7%	—	—	—	—	—
	—	—	PJ[0]	6%	—	7%	—	—	—	—	—
	—	—	PI[15]	6%	—	7%	—	—	—	—	—
	—	—	PI[14]	6%	—	7%	—	—	—	—	—
	2	2	PD[0]	1%	—	1%	—	1%	—	1%	—
			PD[1]	1%	—	1%	—	1%	—	1%	—
			PD[2]	1%	—	1%	—	1%	—	1%	—
			PD[3]	1%	—	1%	—	1%	—	1%	—
			PD[4]	1%	—	1%	—	1%	—	1%	—
			PD[5]	1%	—	1%	—	1%	—	1%	—
			PD[6]	1%	—	1%	—	1%	—	2%	—
			PD[7]	1%	—	1%	—	1%	—	2%	—

Table 24. I/O weight⁽¹⁾ (continued)

Supply segment			Pad	LQFP176				LQFP144/100			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
LQFP 176	LQFP 144	LQFP 100		SRC ⁽²⁾ = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
4	2	2	PD[8]	1%	—	1%	—	1%	—	2%	—
			PB[4]	1%	—	1%	—	1%	—	2%	—
			PB[5]	1%	—	1%	—	1%	—	2%	—
			PB[6]	1%	—	1%	—	1%	—	2%	—
			PB[7]	1%	—	1%	—	1%	—	2%	—
			PD[9]	1%	—	1%	—	1%	—	2%	—
			PD[10]	1%	—	1%	—	1%	—	2%	—
			PD[11]	1%	—	1%	—	1%	—	2%	—

Figure 10. Low voltage detector vs reset

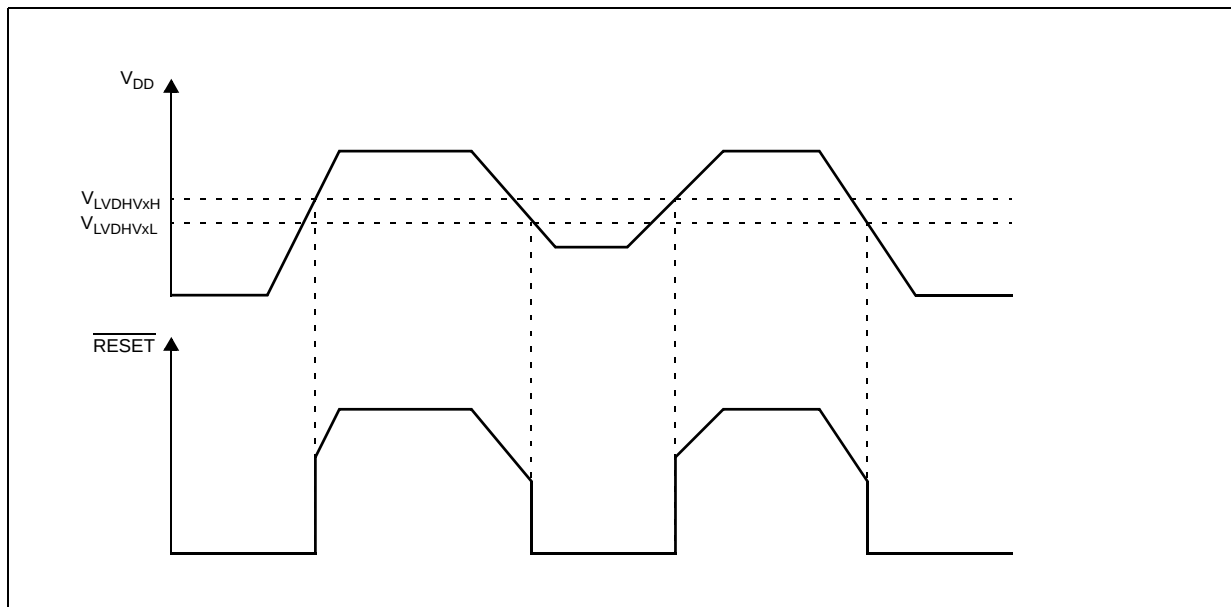


Table 27. Low voltage detector electrical characteristics

Symbol	C	Parameter	Conditions ⁽¹⁾	Value			Unit
				Min	Typ	Max	
V_{PORUP}	SR	P	Supply for functional POR module	1.0	—	5.5	V
V_{PORH}	CC	P	Power-on reset threshold	1.5	—	2.6	
$V_{LVDHV3H}$	CC	T	LVDHV3 low voltage detector high threshold	—	—	2.95	
$V_{LVDHV3L}$	CC	P	LVDHV3 low voltage detector low threshold	2.6	—	2.9	
$V_{LVDHV3BH}$	CC	P	LVDHV3B low voltage detector high threshold	—	—	2.95	
$V_{LVDHV3BL}$	CC	P	LVDHV3B low voltage detector low threshold	2.6	—	2.9	
$V_{LVDHV5H}$	CC	T	LVDHV5 low voltage detector high threshold	—	—	4.5	
$V_{LVDHV5L}$	CC	P	LVDHV5 low voltage detector low threshold	3.8	—	4.4	
$V_{LVDLVCORL}$	CC	P	LVDLVCOR low voltage detector low threshold	1.08	—	1.16	
$V_{LVDLVBKPL}$	CC	P	LVDLVBKP low voltage detector low threshold	1.08	—	1.16	

1. $V_{DD} = 3.3 \text{ V} \pm 10\% / 5.0 \text{ V} \pm 10\%$, $T_A = -40$ to 125°C , unless otherwise specified.

4.9 Power consumption

Table 28 provides DC electrical characteristics for significant application modes. These values are indicative values; actual consumption depends on the application.

Therefore it is recommended that the user apply EMC software optimization and prequalification tests in relation with the EMC level requested for the application.

- Software recommendations – The software flowchart must include the management of runaway conditions such as:
 - Corrupted program counter
 - Unexpected reset
 - Critical data corruption (control registers...)
- Prequalification trials – Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the reset pin or the oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note *Software Techniques For Improving Microcontroller EMC Performance* (AN1015)).

4.11.2 Electromagnetic interference (EMI)

The product is monitored in terms of emission based on a typical application. This emission test conforms to the IEC61967-1 standard, which specifies the general conditions for EMI measurements.

Table 34. EMI radiated emission measurement⁽¹⁾⁽²⁾

Symbol		C	Parameter	Conditions		Value			Unit
						Min	Typ	Max	
—	SR	—	Scan range	—		0.15 0		1000	MHz
f _{CPU}	SR	—	Operating frequency	—		—	64	—	MHz
V _{DD_LV}	SR	—	LV operating voltages	—		—	1.28	—	V
S _{EMI}	CC	T	Peak level	V _{DD} = 5 V, T _A = 25 °C, LQFP144 package Test conforming to IEC 61967-2, f _{OSC} = 8 MHz/f _{CPU} = 64 MHz	No PLL frequency modulation	—	—	18	dBμ V
					± 2% PLL frequency modulation	—	—	14	dBμ V

1. EMI testing and I/O port waveforms per IEC 61967-1, -2, -4.

2. For information on conducted emission and susceptibility measurement (norm IEC 61967-4), please contact your local marketing representative.

4.11.3 Absolute maximum ratings (electrical sensitivity)

Based on two different tests (ESD and LU) using specific measurement methods, the product is stressed in order to determine its performance in terms of electrical sensitivity.

Table 42. Fast internal RC oscillator (16 MHz) electrical characteristics (continued)

Symbol		C	Parameter	Conditions ⁽¹⁾		Value			Unit
						Min	Typ	Max	
I _{FIRCSTOP}	CC	T	Fast internal RC oscillator high frequency and system clock current in stop mode	T _A = 25 °C	sysclk = off	—	500	—	μA
					sysclk = 2 MHz	—	600	—	
					sysclk = 4 MHz	—	700	—	
					sysclk = 8 MHz	—	900	—	
					sysclk = 16 MHz	—	1250	—	
t _{FIRCSU}	CC	C	Fast internal RC oscillator start-up time	V _{DD} = 5.0 V ± 10%		—	1.1	2.0	μs
Δ _{FIRCPRE}	CC	C	Fast internal RC oscillator precision after software trimming of f _{FIRC}	T _A = 25 °C		–1	—	1	%
Δ _{FIRCTRM}	CC	C	Fast internal RC oscillator trimming step	T _A = 25 °C		—	1.6		%
Δ _{FIRCVAR}	CC	C	Fast internal RC oscillator variation over temperature and supply with respect to f _{FIRC} at T _A = 25 °C in high-frequency configuration	—		–5	—	5	%

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.

2. This does not include consumption linked to clock tree toggling and peripherals consumption when RC oscillator is ON.

4.16 Slow internal RC oscillator (128 kHz) electrical characteristics

The device provides a 128 kHz low power internal RC oscillator. This can be used as the reference clock for the RTC module.

Table 43. Slow internal RC oscillator (128 kHz) electrical characteristics

Symbol		C	Parameter	Conditions ⁽¹⁾	Value			Unit
					Min	Typ	Max	
f _{SIRC}	CC	P	Slow internal RC oscillator low frequency	T _A = 25 °C, trimmed	—	128	—	kHz
	SR	—		—	100	—	150	
I _{SIRC} ⁽²⁾	CC	C	Slow internal RC oscillator low frequency current	T _A = 25 °C, trimmed	—	—	5	μA
t _{SIRCSU}	CC	P	Slow internal RC oscillator start-up time	T _A = 25 °C, V _{DD} = 5.0 V ± 10%	—	8	12	μs

Figure 21. ADC_1 characteristic and error definitions

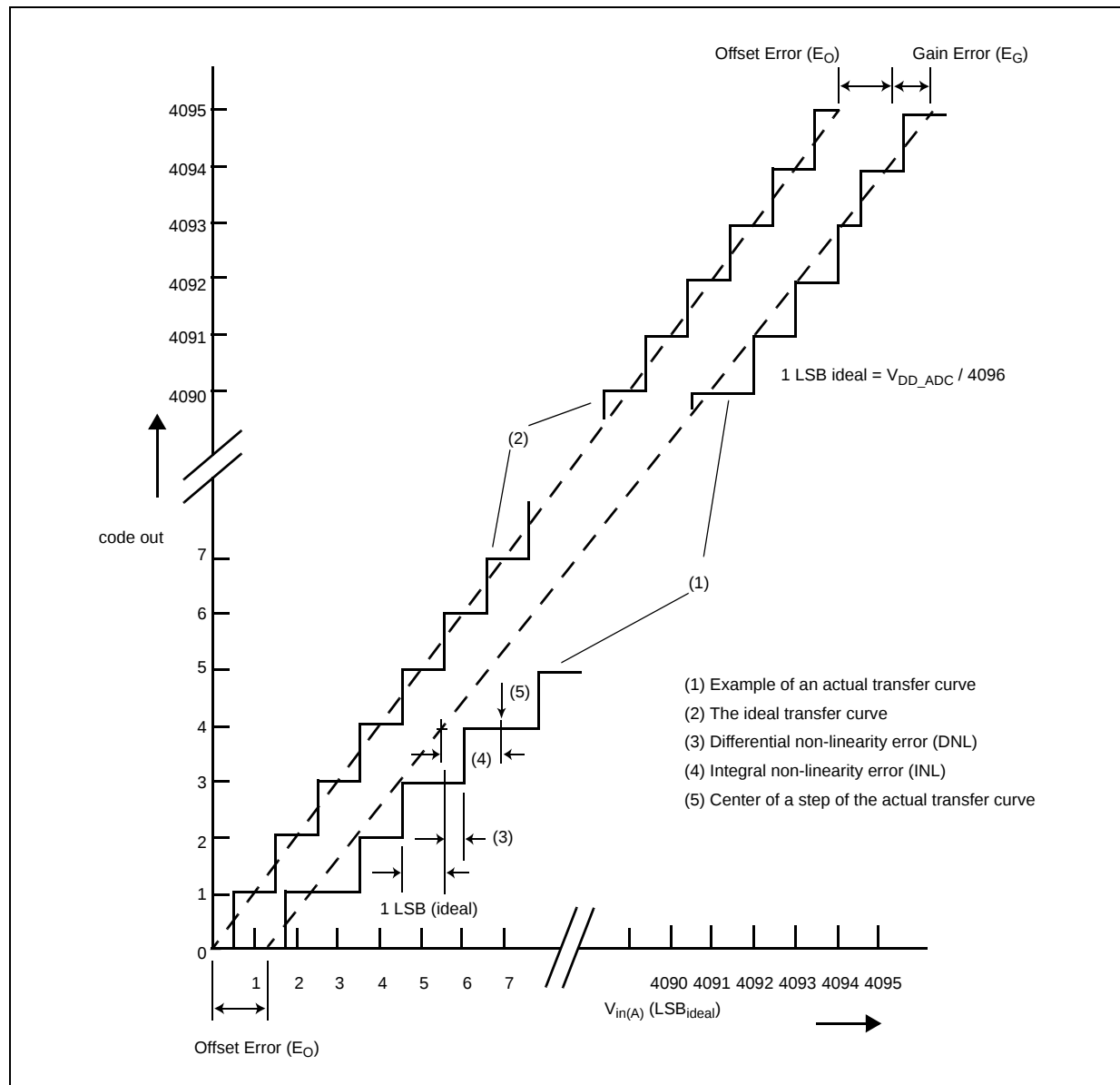


Table 46. ADC_1 conversion characteristics (12-bit ADC_1)

Symbol	C	Parameter	Conditions ⁽¹⁾	Value			Unit
				Min	Typ	Max	
V_{SS_ADC1}	SR	Voltage on VSS_HV_ADC1 (ADC_1 reference) pin with respect to ground (V_{SS}) ⁽²⁾	—	-0.1	—	0.1	V
V_{DD_ADC1}	SR	Voltage on VDD_HV_ADC1 pin (ADC_1 reference) with respect to ground (V_{SS})	—	$V_{DD} - 0.1$	—	$V_{DD} + 0.1$	V
V_{AINx}	SR	Analog input voltage ⁽³⁾	—	$V_{SS_ADC1} - 0.1$	—	$V_{DD_ADC1} + 0.1$	V

Figure 23. DSPI classic SPI timing — master, CPHA = 1

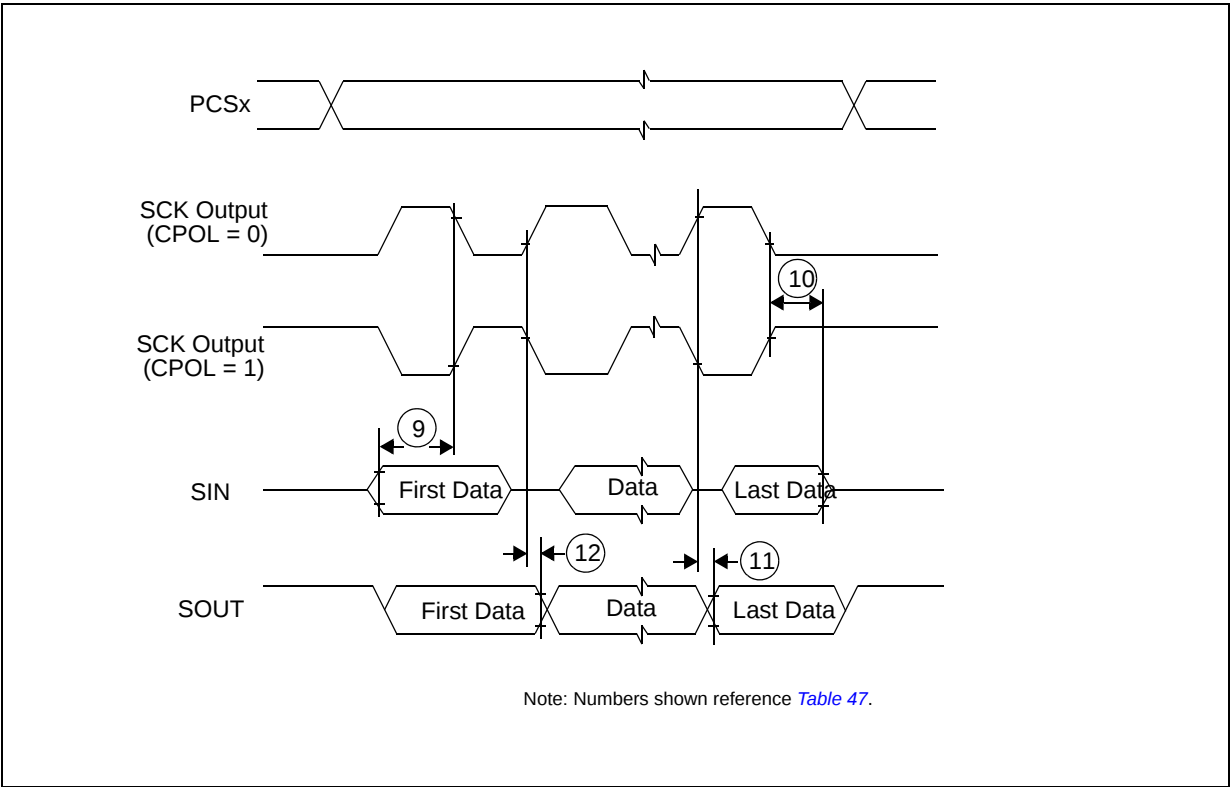


Figure 24. DSPI classic SPI timing — slave, CPHA = 0

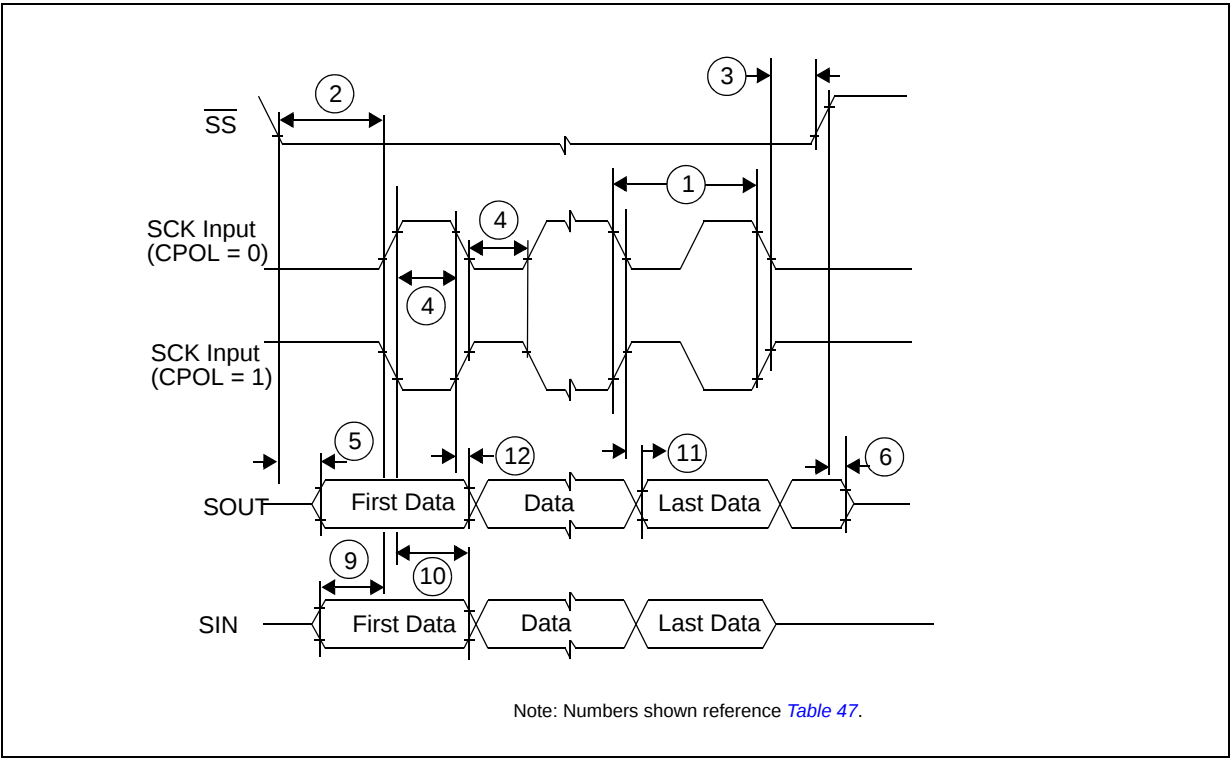


Figure 29. DSPI modified transfer format timing — slave, CPHA = 1

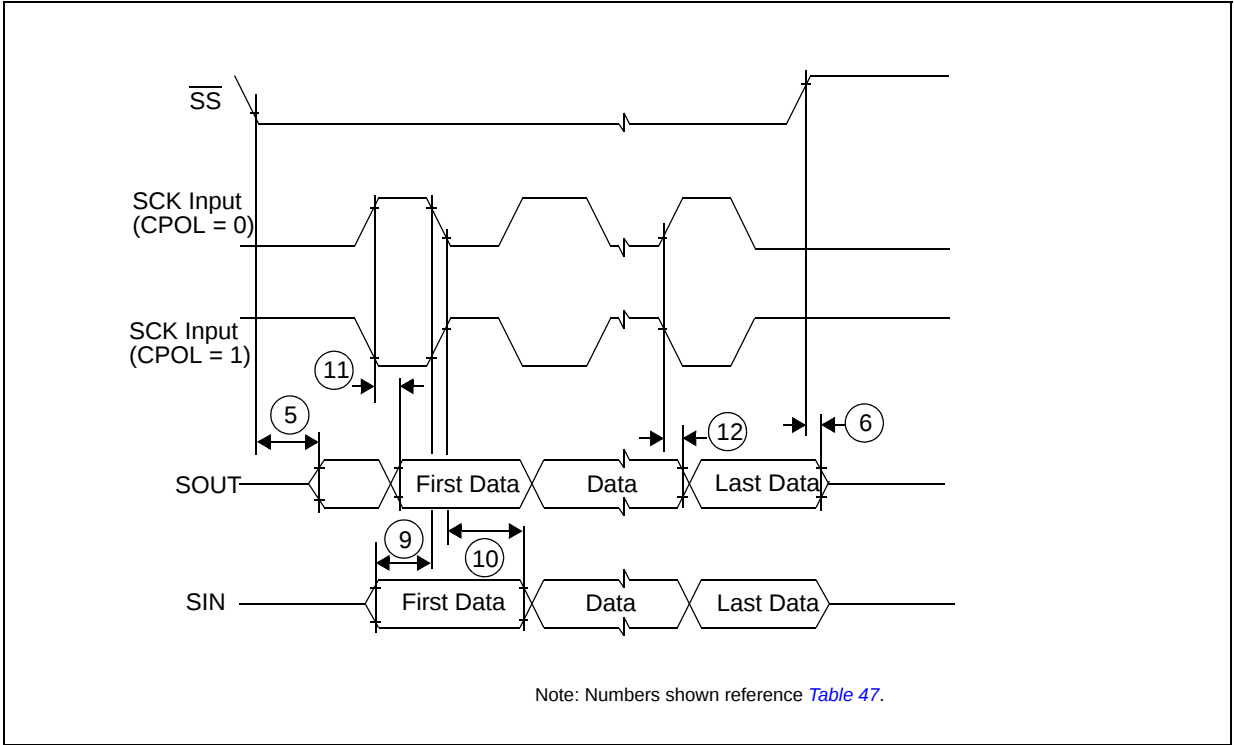
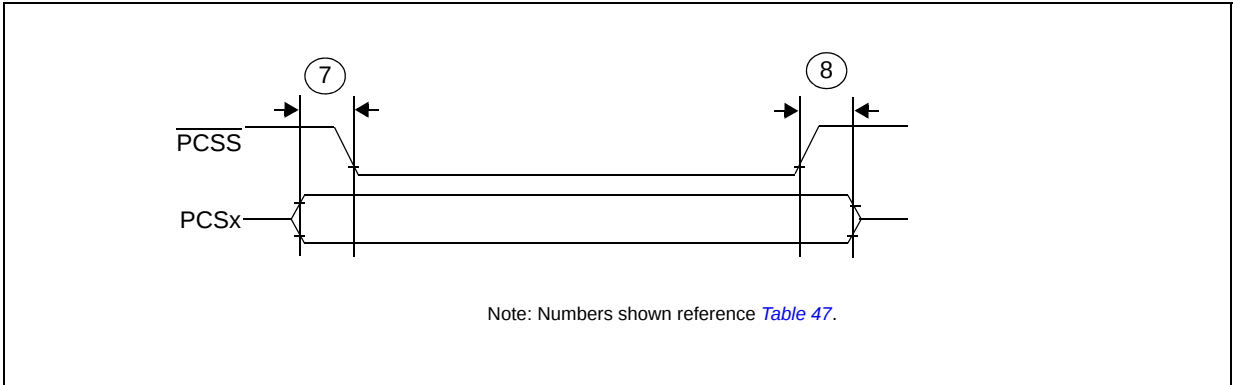


Figure 30. DSPI PCS strobe ($\overline{PCSS}$) timing



4.18.3 Nexus characteristics

Table 49. Nexus characteristics

No.	Symbol	C	Parameter	Value			Unit
				Min	Typ	Max	
1	t_{TCYC}	CC	D TCK cycle time	64	—	—	ns
2	t_{MCYC}	CC	D MCKO cycle time	32	—	—	ns
3	t_{MDOV}	CC	D MCKO low to MDO data valid	—	—	8	ns
4	t_{MSEOV}	CC	D MCKO low to MSEO_b data valid	—	—	8	ns

4.18.4 JTAG characteristics

Table 50. JTAG characteristics

No.	Symbol		C	Parameter	Value			Unit
					Min	Typ	Max	
1	t _{JCYC}	CC	D	TCK cycle time	64	—	—	ns
2	t _{TDIS}	CC	D	TDI setup time	15	—	—	ns
3	t _{TDIH}	CC	D	TDI hold time	5	—	—	ns
4	t _{TMSS}	CC	D	TMS setup time	15	—	—	ns
5	t _{TMSH}	CC	D	TMS hold time	5	—	—	ns
6	t _{TDOV}	CC	D	TCK low to TDO valid	—	—	33	ns
7	t _{TDOI}	CC	D	TCK low to TDO invalid	6	—	—	ns

Figure 32. Timing diagram — JTAG boundary scan

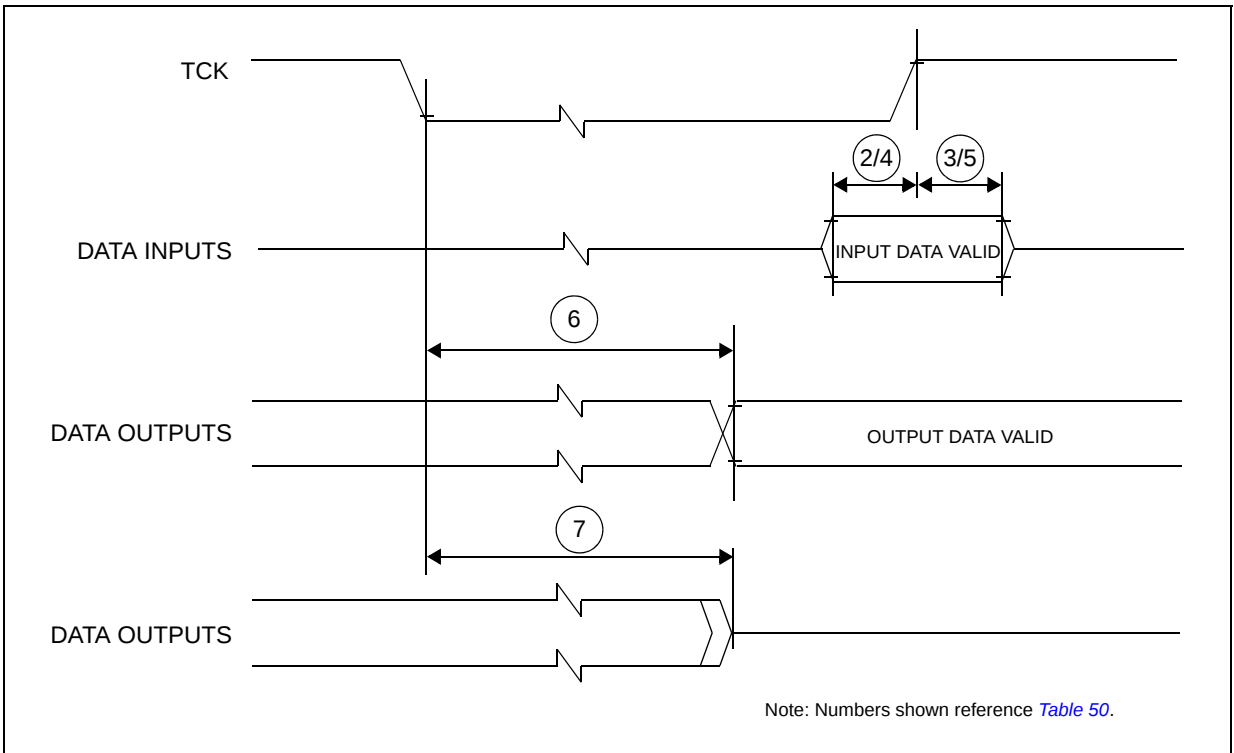


Table 51. LQFP176 mechanical data⁽¹⁾

Symbol	mm			inches ⁽²⁾		
	Min	Typ	Max	Min	Typ	Max
A	1.400	—	1.600		—	0.063
A1	0.050	—	0.150	0.002	—	
A2	1.350	—	1.450	0.053	—	0.057
b	0.170	—	0.270	0.007	—	0.011
C	0.090	—	0.200	0.004	—	0.008
D	23.900	—	24.100	0.941	—	0.949
E	23.900	—	24.100	0.941	—	0.949
e	—	0.500	—	—	0.020	—
HD	25.900	—	26.100	1.020	—	1.028
HE	25.900	—	26.100	1.020	—	1.028
L ⁽³⁾	0.450	—	0.750	0.018	—	0.030
L1	—	1.000	—	—	0.039	—
ZD	—	1.250	—	—	0.049	—
ZE	—	1.250	—	—	0.049	—
q	0 °	—	7 °	0 °	—	7 °
Tolerance	mm			inches		
ccc	0.080			0.0031		

1. Controlling dimension: millimeter.

2. Values in inches are converted from mm and rounded to 4 decimal digits.

3. L dimension is measured at gauge plane at 0.25 mm above the seating plane.

Table 56. Revision history (continued)

Date	Revision	Changes
12-Sep- 2011 (continued)	6 (continued)	Section "Program/erase characteristics": removed table "FLASH_BIU settings vs. frequency of operation" and associated introduction "Program and erase specifications" table: updated symbols PFCRn settings vs. frequency of operation: replaced "FLASH_BIU" with "PFCRn" in table title; updated field names and frequencies "Flash power supply DC electrical characteristics" table: deleted footnote 2 Crystal oscillator and resonator connection scheme: inserted footnote about possibly requiring a series resistor Fast external crystal oscillator (4 to 16 MHz) electrical characteristics: updated parameter classification for $V_{FXOSCOP}$ Slow external crystal oscillator (32 kHz) electrical characteristics: updated footnote 1 Section "ADC electrical characteristics": updated symbols for offset error and gain error Section "Input impedance and ADC accuracy": changed "V_A/V_{A2}" to "V_{A2}/V_A" in Equation 11 ADC input leakage current: updated I_{LKG} characteristics ADC_0 conversion characteristics table: replaced instances of "ADCx_conf_sample_input" with "INPSAMP"; replaced instances of "ADCx_conf_comp" with "INPCMP" ADC_1 characteristic and error definitions: replaced "AVDD" with "V_{DD_ADC}" ADC_1 conversion characteristics table: replaced instances of "ADCx_conf_sample_input" with "INPSAMP"; replaced instances of "ADCx_conf_comp" with "INPCMP" Updated "On-chip peripherals current consumption" table Removed order codes tables.
18-Sep-2013	7	Updated Disclaimer.
05-May-2014	8	Table 13: Recommended operating conditions (3.3 V), added minimum value of T_{VDD} and footnote about it. Table 14: Recommended operating conditions (5.0 V), added minimum value of T_{VDD} and footnote about it. Table 21: Output pin transition times, replaced T_{tr} with t_{tr} Table 25: Reset electrical characteristics, replaced T_{tr} with t_{tr} Updated Section 4.17.2: Input impedance and ADC accuracy Table 27: Low voltage detector electrical characteristics, changed $V_{LVDHV3L}(\min)$ and $V_{LVDHV3BL}(\min)$ from 2.7 V to 2.6 V. Table 29: Program and erase specifications, added footnote about t_{ESRT} Table 41: FMPLL electrical characteristics, deleted footnote relative to maximum value of f_{CPU} Table 45: ADC_0 conversion characteristics (10-bit ADC_0), changed $I_{ADC0run}$ value from 40 mA to 5 mA. Table 48: DSPI characteristics, in the heading row, replaced DSPI0/DSPI1/DSPI5/DSPI6 with DSPI0/DSPI1/DSPI3/DSPI5.
22-Jan-2016	9	In Table 1: Device summary, added SPC560B64L3 for 1.5 MB code flash devices. In Table 2: SPC560B54/6x family comparison, added column relating to "LQFP100" package in SPC560B64 devices. In Table 28: Power consumption on VDD_BV and VDD_HV: – changed footnote 2 "Running consumption does not include I/Os..." to "I_{DDMAX} is drawn only from the VDD_BV pin. Running consumption does not include I/Os..." – changed footnote 4 "RUN current measured with..." to "I_{DDRUN} is drawn only from the VDD_BV pin. RUN current measured with..."